

Yongjin Lee

List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/102549/publications.pdf>

Version: 2024-02-01

14
papers

739
citations

758635

12
h-index

1058022

14
g-index

14
all docs

14
docs citations

14
times ranked

1120
citing authors

#	ARTICLE	IF	CITATIONS
1	Tunable Valley Splitting due to Topological Orbital Magnetic Moment in Bilayer Graphene Quantum Point Contacts. <i>Physical Review Letters</i> , 2020, 124, 126802.	2.9	46
2	The electronic thickness of graphene. <i>Science Advances</i> , 2020, 6, eaay8409.	4.7	35
3	Charge Detection in Gate-Defined Bilayer Graphene Quantum Dots. <i>Nano Letters</i> , 2019, 19, 5216-5221.	4.5	45
4	Gap Opening in Twisted Double Bilayer Graphene by Crystal Fields. <i>Nano Letters</i> , 2019, 19, 8821-8828.	4.5	39
5	Electrostatically Induced Quantum Point Contacts in Bilayer Graphene. <i>Nano Letters</i> , 2018, 18, 553-559.	4.5	83
6	Gate-tunable quantum dot in a high quality single layer MoS ₂ van der Waals heterostructure. <i>Applied Physics Letters</i> , 2018, 112, .	1.5	60
7	Interactions and Magnetotransport through Spin-Valley Coupled Landau Levels in Monolayer MoS ₂ . <i>Physical Review Letters</i> , 2018, 121, 247701.	2.9	80
8	Transport Through a Network of Topological Channels in Twisted Bilayer Graphene. <i>Nano Letters</i> , 2018, 18, 6725-6730.	4.5	109
9	Gate-Defined Quantum Confinement in InSe-Based van der Waals Heterostructures. <i>Nano Letters</i> , 2018, 18, 3950-3955.	4.5	40
10	Spin and Valley States in Gate-Defined Bilayer Graphene Quantum Dots. <i>Physical Review X</i> , 2018, 8, .	2.8	83
11	Coupled Quantum Dots in Bilayer Graphene. <i>Nano Letters</i> , 2018, 18, 5042-5048.	4.5	64
12	Magnetotransport and lateral confinement in an InSe van der Waals Heterostructure. <i>2D Materials</i> , 2018, 5, 035040.	2.0	7
13	Oscillating Magnetoresistance in Graphene p-n Junctions at Intermediate Magnetic Fields. <i>Nano Letters</i> , 2017, 17, 2852-2857.	4.5	9
14	Gate-Defined One-Dimensional Channel and Broken Symmetry States in MoS ₂ van der Waals Heterostructures. <i>Nano Letters</i> , 2017, 17, 5008-5011.	4.5	39